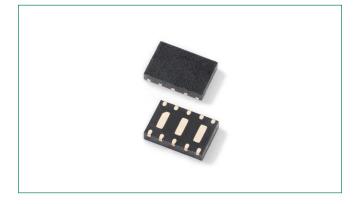
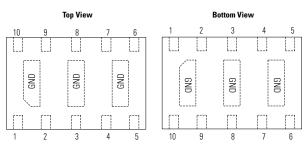


SP2574NUTG 2.5V 40A Diode Array

RoHS 🗭 GREEN

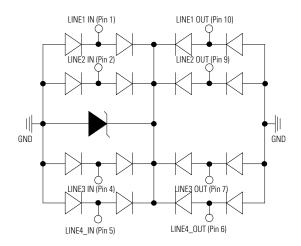


Pinout



NOTE: PIN3, PIN8 are same potential with GND

Functional Block Diagram



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Description

The SP2574NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for high-speed, differential data lines. It's packaged in a μ DFN package (3.0 x 2.0mm) and each component can protect up 4 channels or 2 differential pairs, up to 40A (IEC 61000-4-5) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The SP2574NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

• µDFN-10 package is

data line routing

· Low operating and

clamping voltage

• AEC-Q101 gualified

LVDS Interfaces

Smart TV

Integrated Magnetics

 Provides protection for two differential data pairs

(4 channels) up to 40A

optimized for high-speed

Features

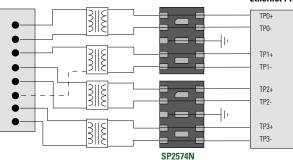
- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 40A (8/20µs as defined in IEC 61000-4-5 2nd Edition)
- Low capacitance of 3.8pF@0V (TYP) per I/O
- Low leakage current of 0.1µA (TYP) at 2.5V

Applications

- •10/100/1000 Ethernet
- WAN/LAN Equipment
- Desktops, Servers and Notebooks

Application Example

RJ-45 Connector



Ethernet PHY

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
l _{pp}	Peak Current (t _p =8/20µs)	40 ¹	А
P _{Pk}	Peak Pulse Power (t _p =8/20µs)	1000	W
T _{op}	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

Notes:1. Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

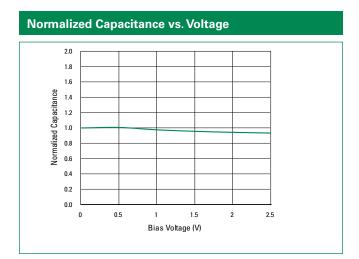
Electrical Characteristics (T_{OP}=25°C)

				_		
Parameter	Symbol	Test Conditions	Min	Тур	Мах	Units
Reverse Standoff Voltage	V _{RVVM}	$I_R \le 1\mu A$			2.5	V
Reverse Leakage Current	I _R	$V_{RWM} = 2.5V, T = 25^{\circ}C$		0.1	0.5	μA
Breakdown Voltage	V _{BR}	$I_{t1} = 1\mu A$	3.0	3.7	4.5	V
Snap Back Voltage	V _{SB}	$I_{H} = 1mA$	3.0			V
Clamp Voltage		$I_{pp} = 1A$, $t_p = 8/20\mu s$ Any I/O to Ground			4.5	V μΑ V
		$I_{pp} = 10A$, $t_p = 8/20\mu s$ Any I/O to Ground			7.5	
	V _c	$I_{pp} = 25A, t_p = 8/20\mu s$ Any I/O to Ground			12.0	
		$I_{pp} = 40$ A, $t_p = 8/20 \mu s$ Line-to-Line ¹ , two I/O Pins connected together on each line			20.0	
Dynamic Resistance ²	R _{DYN}	TLP, t_p =100ns, Any I/O to Ground		0.13		Ω
ESD Withstand Voltage	N	IEC 61000-4-2 (Contact)	±30			kV
	V _{ESD}	IEC 61000-4-2 (Air)	±30			μΑ V V V V Λ Ω KV kV pF
Diode Capacitance	C _{I/O to GND}	Between I/O Pins and Ground $V_{_{ m R}}$ = 0V, f = 1MHz		3.8	5.0	pF
	C _{I/O to I/O}	Between I/O Pins $V_{_{ m R}}$ = 0V, f = 1MHz		1.7		pF

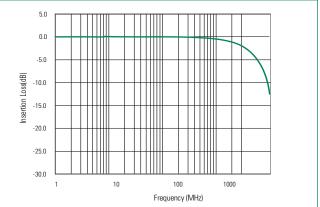
Notes:

1. Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)

2. Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns

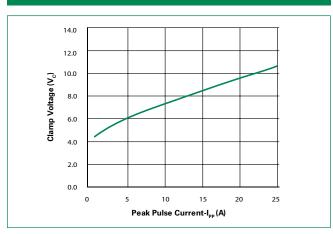




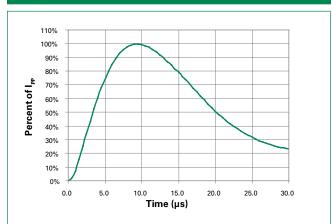


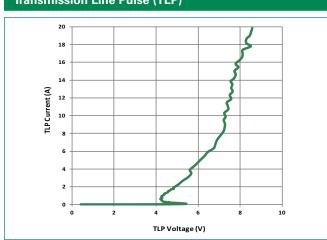


Clamping Voltage vs. I_{PP} (I/O to GND)



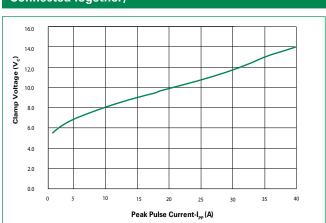
8/20µs Pulse Waveform



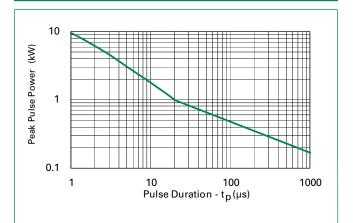


Transmission Line Pulse (TLP)

Clamping Voltage vs. I_{pp} (Line-to-Line, Two I/O Pins Connected Together)



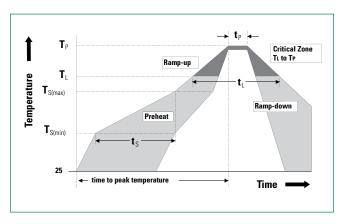
Non-Repetitive Peak Pulse Power vs. Pulse Time





Soldering Parameters

Reflow Con	Pb – Free assembly		
Pre Heat	- Temperature Min (T _{s(min)})	150°C	
	- Temperature Max (T _{s(max)})	200°C	
	- Time (min to max) (t _s)	60 – 180 secs	
Average ran	3°C/second max		
T _{S(max)} to T _L - Ramp-up Rate		3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	- Temperature (t _L)	60 – 150 seconds	
Peak Temperature (T _P)		260+0/-5 °C	
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (T _P)		8 minutes Max.	
Do not exce	260°C		



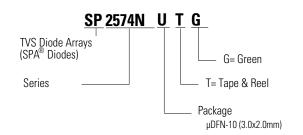
Product Characteristics

Lead Plating	Pre-Plated Frame		
Lead Material	Copper Alloy		
Lead Coplanarity	0.004 inches(0.102mm)		
Substrate material	Silicon		
Body Material	Molded Compound		
Flammability	UL Recognized compound meeting flammability rating V-0		

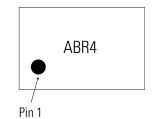
Ordering Information

Part Number	Package	Min. Order Qty.	
SP2574NUTG	µDFN-10 (3.0x2.0mm)	3000	

Part Numbering System



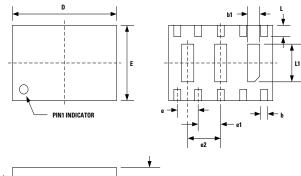
Part Marking System





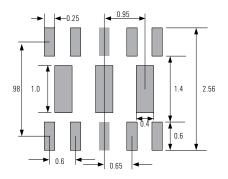
TVS Diode Array (SPA®Diodes) Lightning Surge Protection - SP2574NUTG

Package Dimensions - µDFN-10 (3.0x2.0mm)









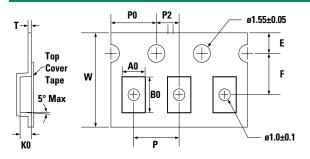
Package	μDFN-10 (3.0x2.0mm)						
JEDEC		MO-229					
Cumhal	Millimeters			Inches			
Symbol	Min	Nom	Max	Min	Nom	Max	
Α	0.50	0.60	0.65	0.020	0.024	0.026	
A1	0.00	0.03	0.05	0.000	0.001	0.002	
A3	0.15 Ref 0.006 Ref			0.006 Ref			
b	0.15	0.20	0.25	0.006	0.008	0.010	
b1	0.25	0.35	0.45	0.010	0.014	0.018	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.90	2.00	2.10	0.075	0.079	0.083	
е		0.60 BSC 0.024 BSC					
e1		0.65 BSC 0.026 BSC					
e2	0.95 BSC 0.037						
L	0.25	0.30	0.35	0.010	0.012	0.014	
L1	0.95	1.00	1.05	0.037	0.039	0.041	

Notes :

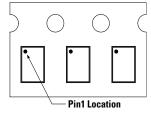
1. All dimensions are in millimeters

Dimensions include solder plating.
 Dimensions are exclusive of mold flash & metal burr

Tape & Reel Specification - µDFN-10 (3.0x2.0mm)



Device Orientation in Tape



Package	μDFN-10 (3.0x2.0mm)		
Symbol	Millimeters		
A0	2.30 +/- 0.10		
B0	3.20 +/- 0.10		
E	1.75 +/- 0.10		
F	3.50 +/- 0.05		
KO	1.0 +/- 0.10		
Р	4.00 +/- 0.10		
PO	4.00 +/- 0.10		
P2	2.00 +/- 0.10		
т	0.3 +/- 0.05		
W	8.00 + 0.30 /- 0.10		

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